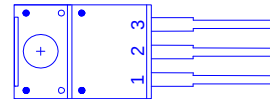
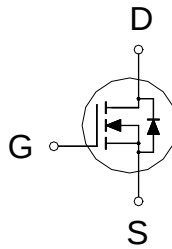




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
600V	0.75Ω	10A



1. GATE
2. DRAIN
3. SOURCE

100% UIS tested

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	± 30	V
Continuous Drain Current ²	$T_C = 25^\circ\text{C}$	I_D	10	A
	$T_C = 100^\circ\text{C}$		6	
Pulsed Drain Current ^{1, 2}		I_{DM}	30	
Avalanche Current ³		I_{AS}	3.5	
Avalanche Energy ³		EAS	61	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	39	W
	$T_C = 100^\circ\text{C}$		15	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3.2	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		62.5	

¹Pulse width limited by maximum junction temperature.

²Limited only by maximum temperature allowed

³ $V_{DD} = 100\text{V}$, $L = 10\text{mH}$, starting $T_J = 25^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	2.9	4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 30V$			± 100	nA

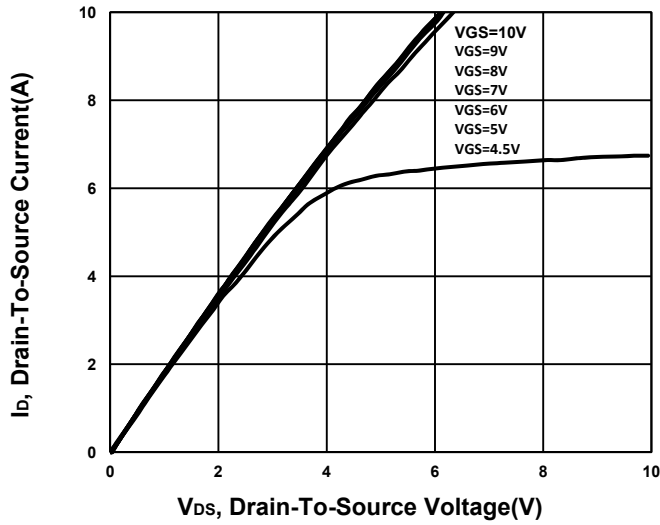
Gate Voltage Drain Current	I _{DSS}	V _{DS} = 600V, V _{GS} = 0V , T _C = 25 °C			1	μA
		V _{DS} = 480V, V _{GS} = 0V , T _C = 100 °C			10	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 5A		0.57	0.75	Ω
Forward Transconductance ¹	g _{fs}	V _{DS} = 15V, I _D = 5A		15		S
DYNAMIC						
Input Capacitance	C _{iSS}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		1552		pF
Output Capacitance	C _{oSS}			162		
Reverse Transfer Capacitance	C _{rSS}			23		
Total Gate Charge ²	Q _g	V _{DD} = 480V, I _D = 10A, V _{GS} = 10V		49		nC
Gate-Source Charge ²	Q _{gs}			7		
Gate-Drain Charge ²	Q _{gd}			20		
Turn-On Delay Time ²	t _{d(on)}	V _{DD} = 300V, I _D = 10A, R _G = 25 Ω		60		nS
Rise Time ²	t _r			34		
Turn-Off Delay Time ²	t _{d(off)}			220		
Fall Time ²	t _f			47		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _J = 25 °C)						
Continuous Current ³	I _S				10	A
Forward Voltage ¹	V _{SD}	I _F =10A, V _{GS} = 0V			1.5	V
Reverse Recovery Time	t _{rr}	I _F = 10A, dI _F /dt = 100A / μS		404		nS
Reverse Recovery Charge	Q _{rr}			4.7		uC

¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

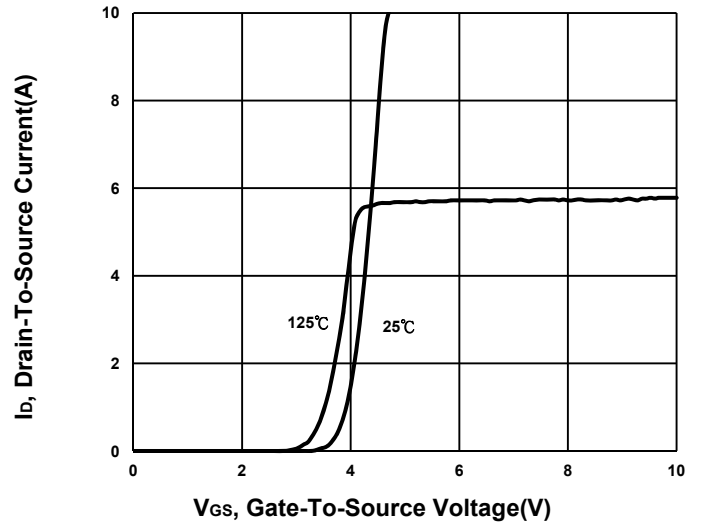
²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

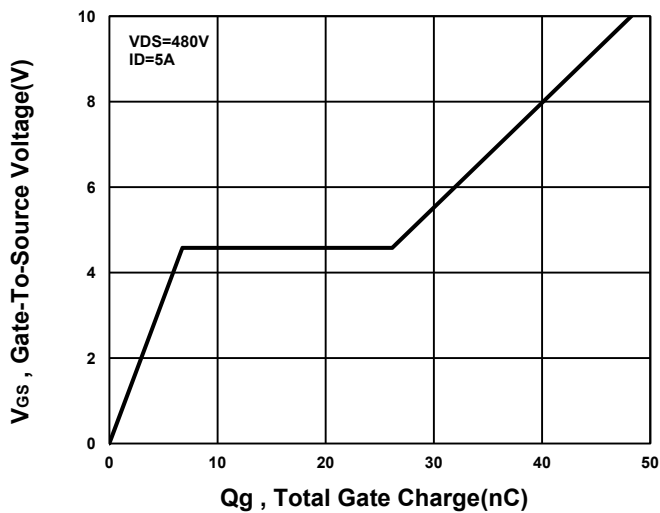
Output Characteristics



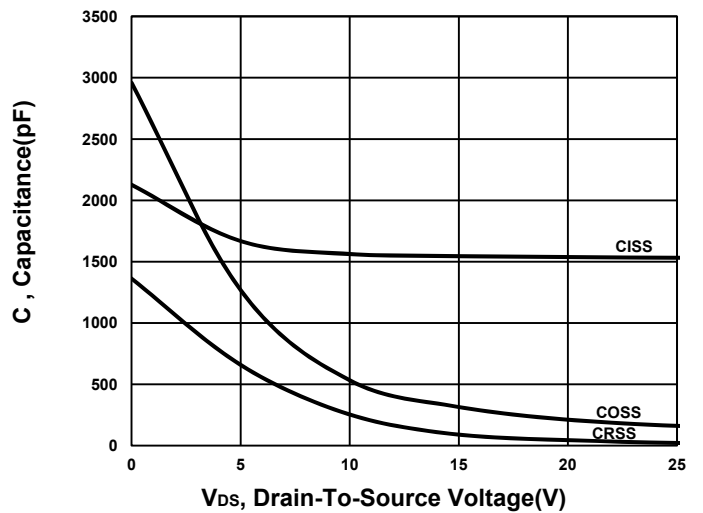
Transfer Characteristics



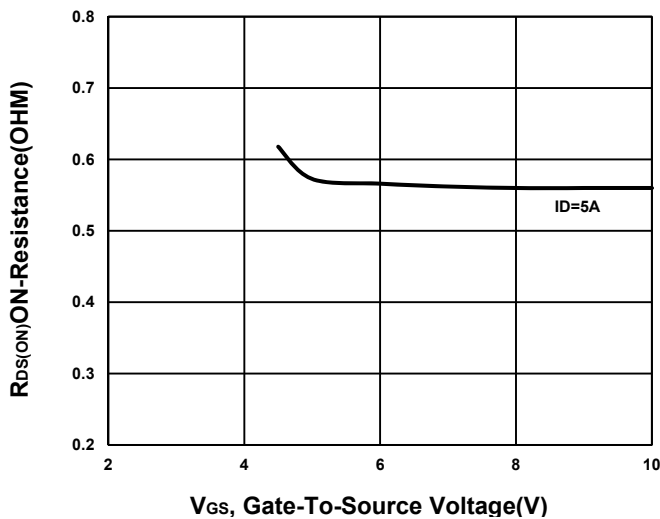
Gate charge Characteristics



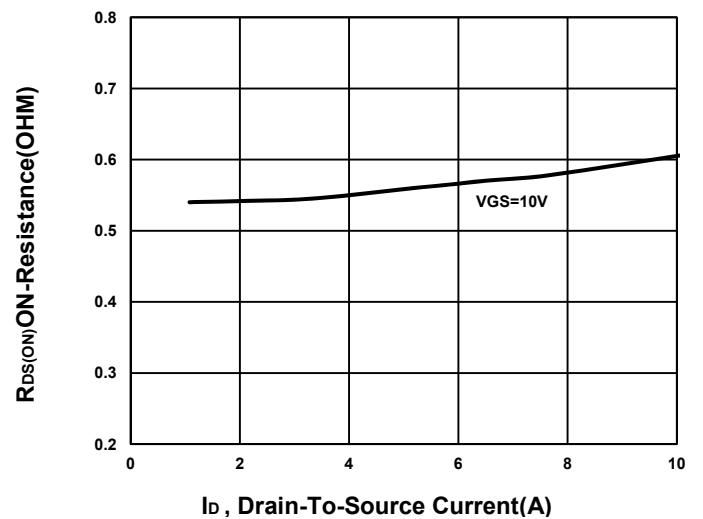
Capacitance Characteristic



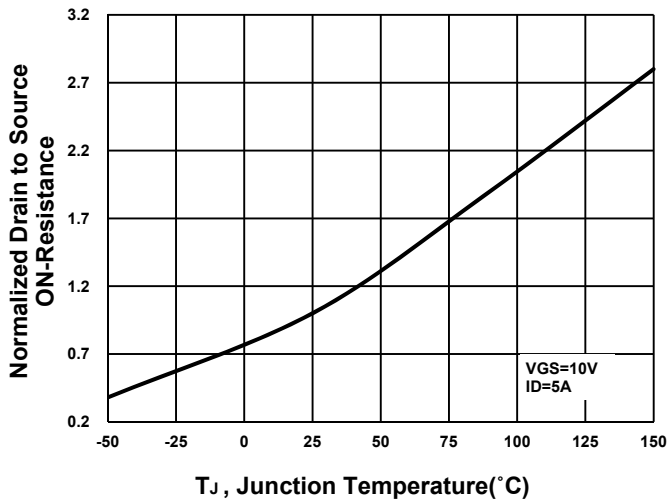
On-Resistance VS Gate-To-Source



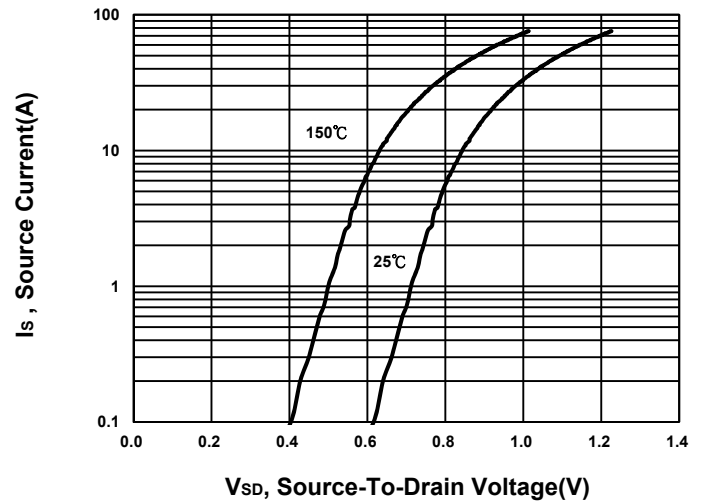
On-Resistance VS Drain Current



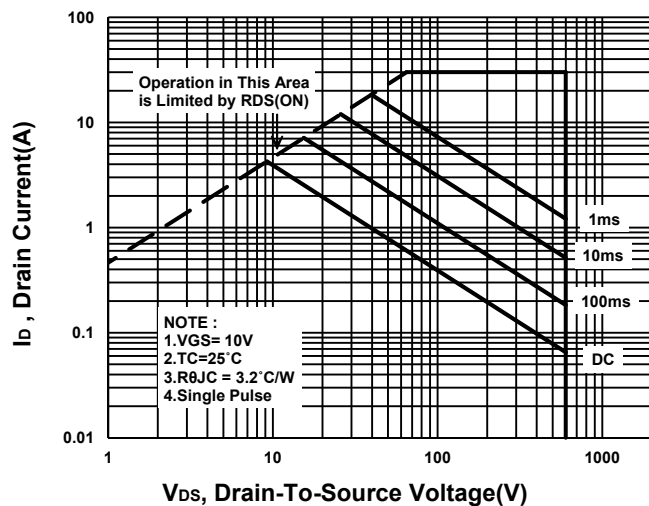
On-Resistance VS Temperature



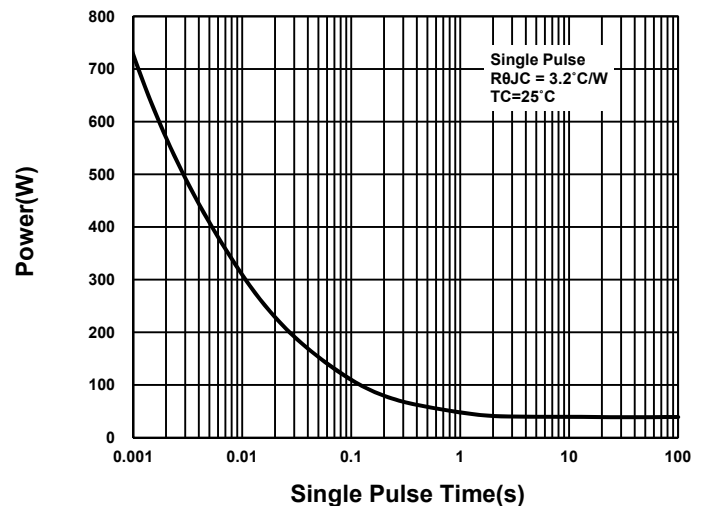
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

